

forming a mask layer above the second antireflective coating,
wherein the mask layer covers selected portions of the second antireflective coating
and exposes other portions of the second antireflective coating;

a' etching [through a portion of] the first antireflective coating, [a portion of] the second antireflective coating, and [a portion of] the wiring line layer, at the location where the second antireflective coating is exposed by the mask layer, to form wiring lines separated by gaps; and

depositing a dielectric material within the gaps [between the wiring lines] to fill the gaps, using high density plasma chemical vapor deposition.

[Claim 2, line 1, delete "primarily".

Claim 2, line 2, delete "primarily".

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a⁴ ~~33~~ The method of claim 1, wherein the [dielectric material within the gaps deposited using high density plasma chemical vapor deposition] mask layer is a patterned photoresist layer.

[Claim 4, line 1, replace "claim 3" with --claim 1--.

a² 9. (Once amended) A method for forming conducting structures separated by gaps on a substrate, comprising:

providing a substrate and a wiring line layer above the substrate;

forming a cap layer above the wiring line layer;

forming a mask layer above the cap layer, wherein the mask layer covers selected portions of the cap layer and exposes other portions of the cap layer;

etching [through a portion of] the cap layer, [a portion of] and [a portion of] the wiring line layer, at the locations where the cap layer is exposed by the mask layer, to form wiring lines separated by gaps, the wiring lines having a remaining portion of the cap layer thereon; and

[deposition] depositing a dielectric material [using high density plasma chemical vapor deposition] within the gaps [between the wiring lines] at a sputtering rate sufficient to fill the gaps, using high density plasma chemical vapor deposition.

Claim 20, line 18, insert --and-- at the end of the line.

Claim 20, line 20, insert --to fill the gaps-- at the end of the line.

²⁰
~~21~~. The method of claim 9, wherein the mask layer is a patterned photoresist layer.--

REMARKS

Claims 1, 2, 4, 9, and 20 have been amended. ~~Claim 3 has been canceled.~~

A new dependent claim 21 has been added to further protect the invention.

Examination of the amended application is respectfully requested. Claims 1-20 stand rejected under 35 U.S.C. § 112, first paragraph, as failing to disclose subject matter which would enable one skilled in the art to make and use the invention.

Applicants have amended claims 1, 2, 4, 9, and 20 in response to the Examiner's

AMENDMENT